

FIG. 1A

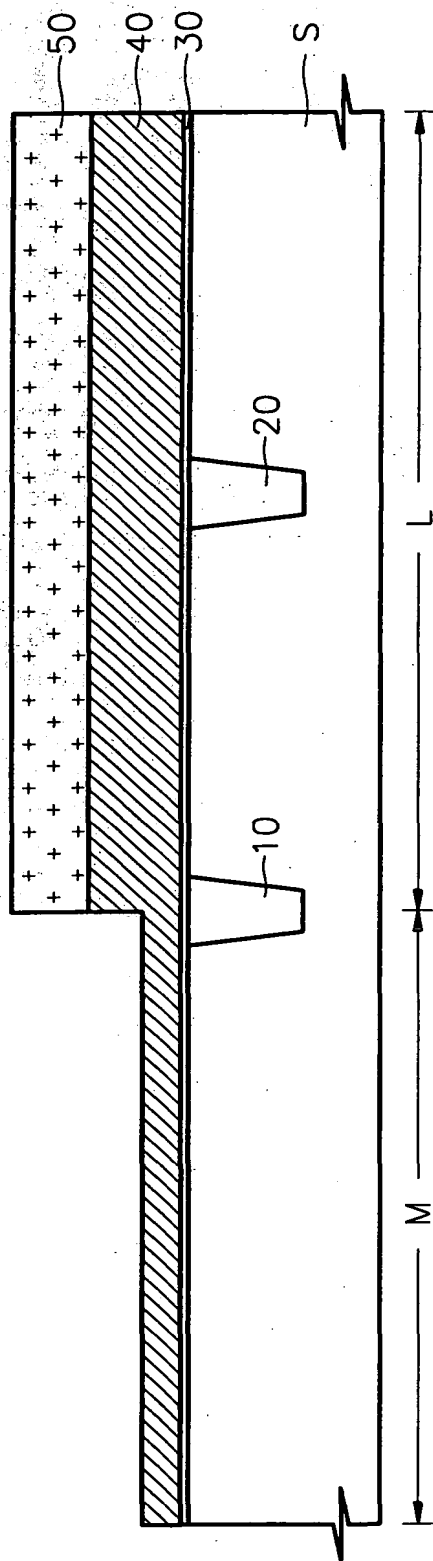


FIG. 1B

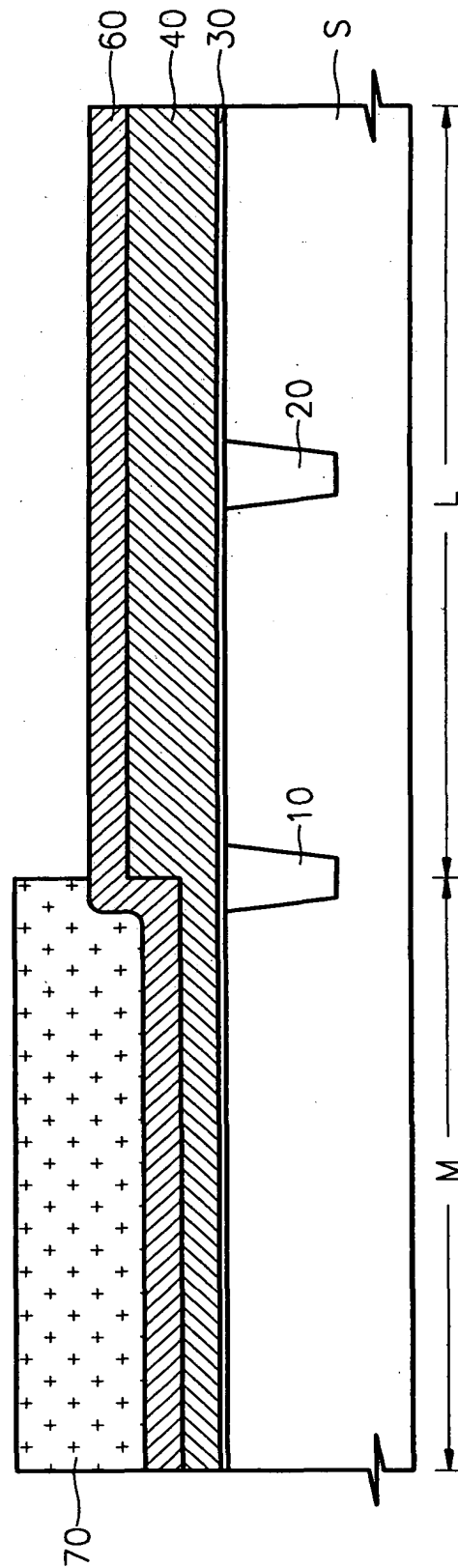


FIG. 1C

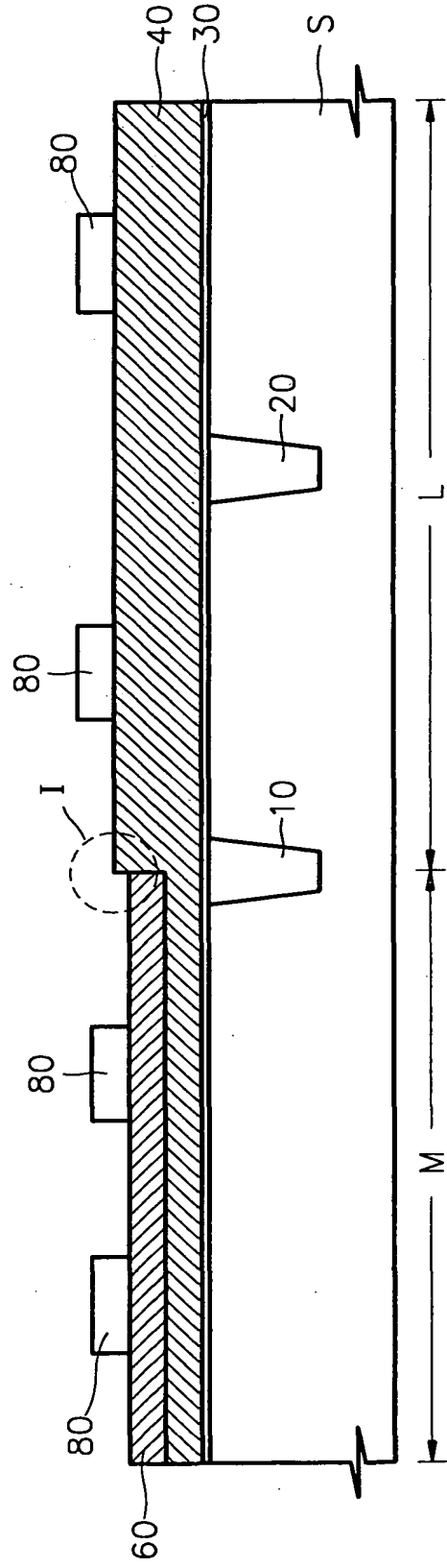


FIG. 1D

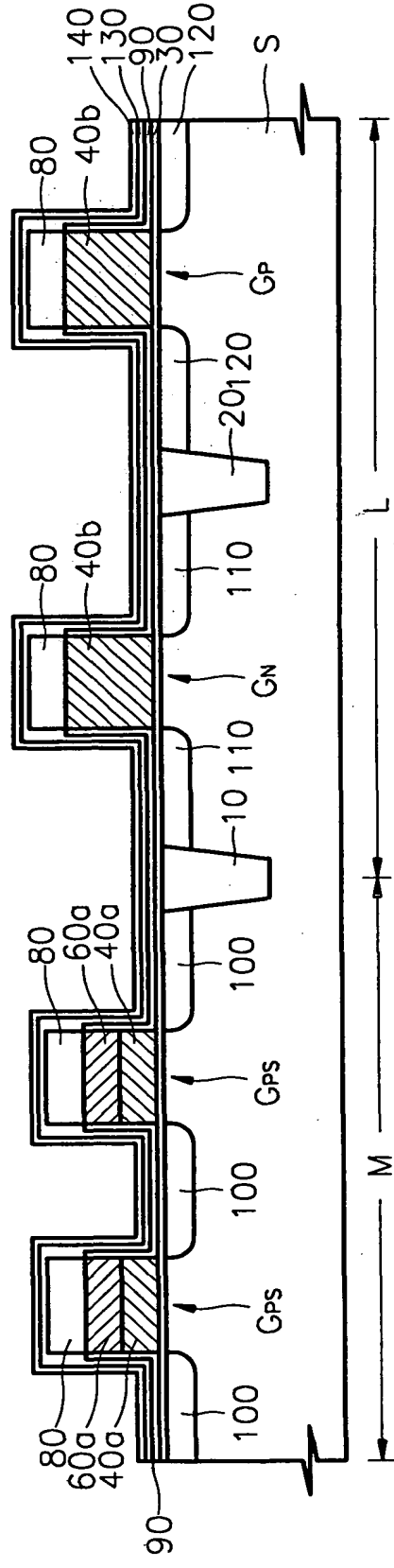


FIG. 1E

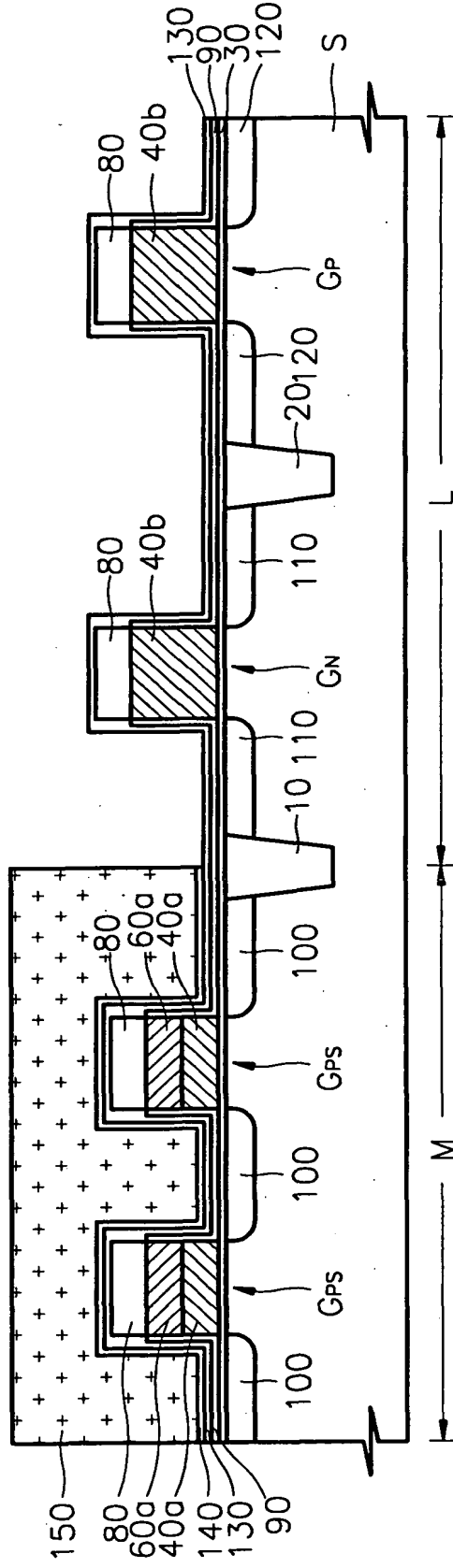


FIG. 1F

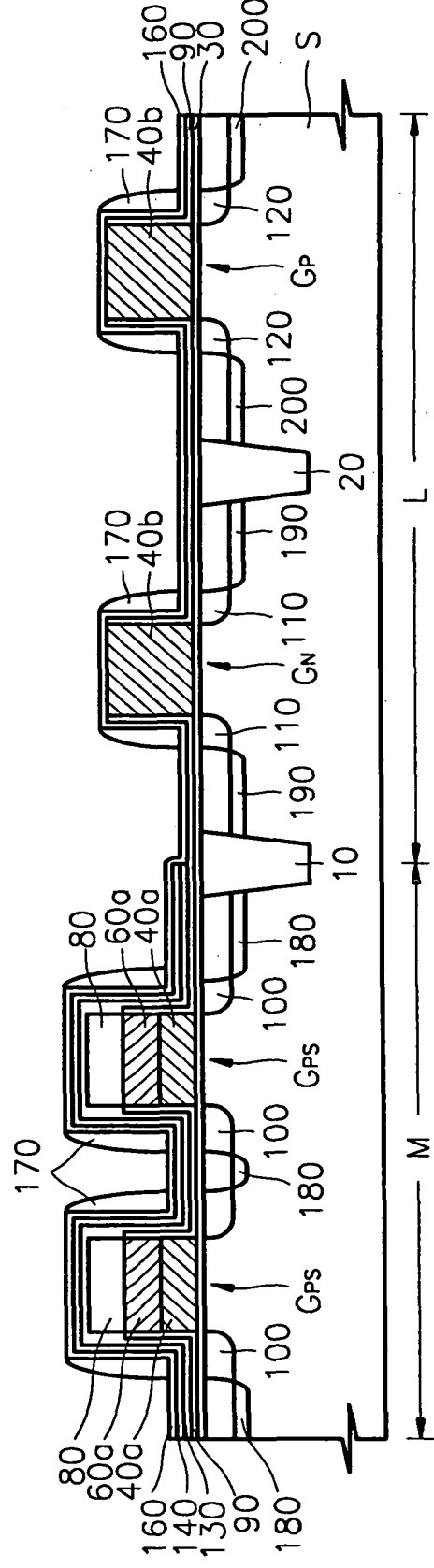


FIG. 1G

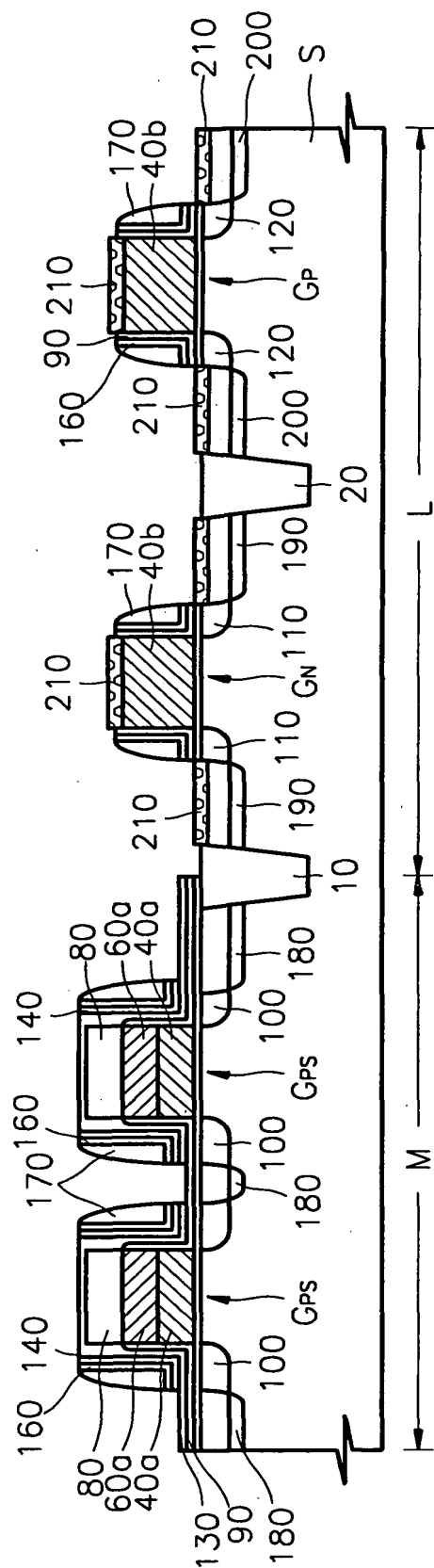


FIG. 1H

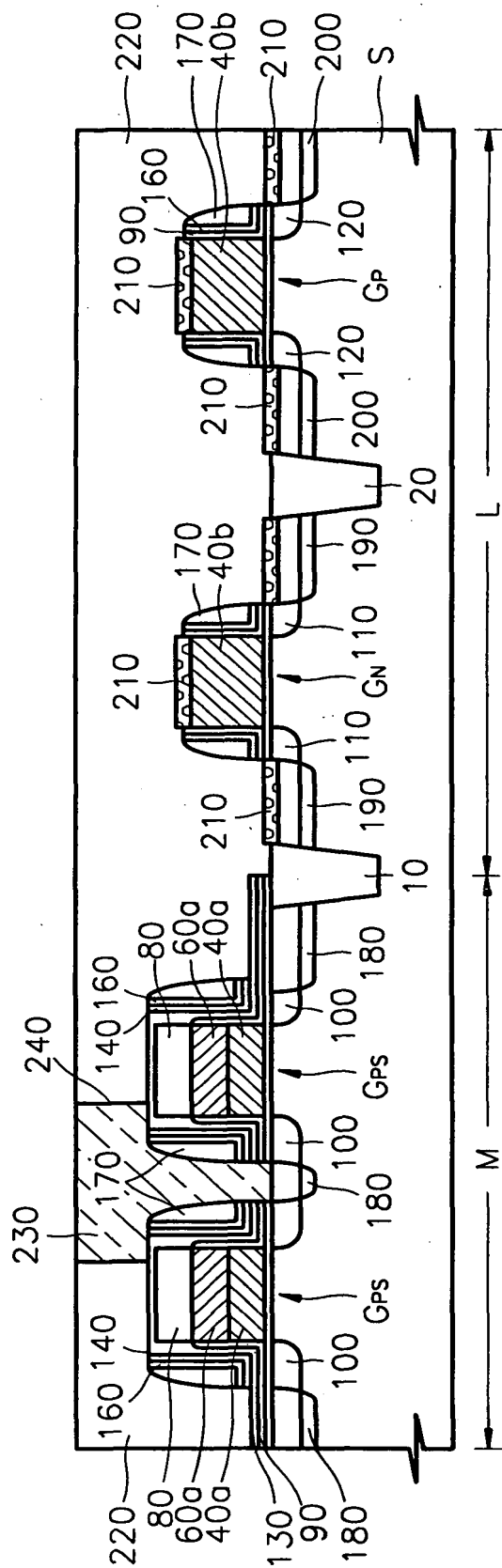


FIG. 2A

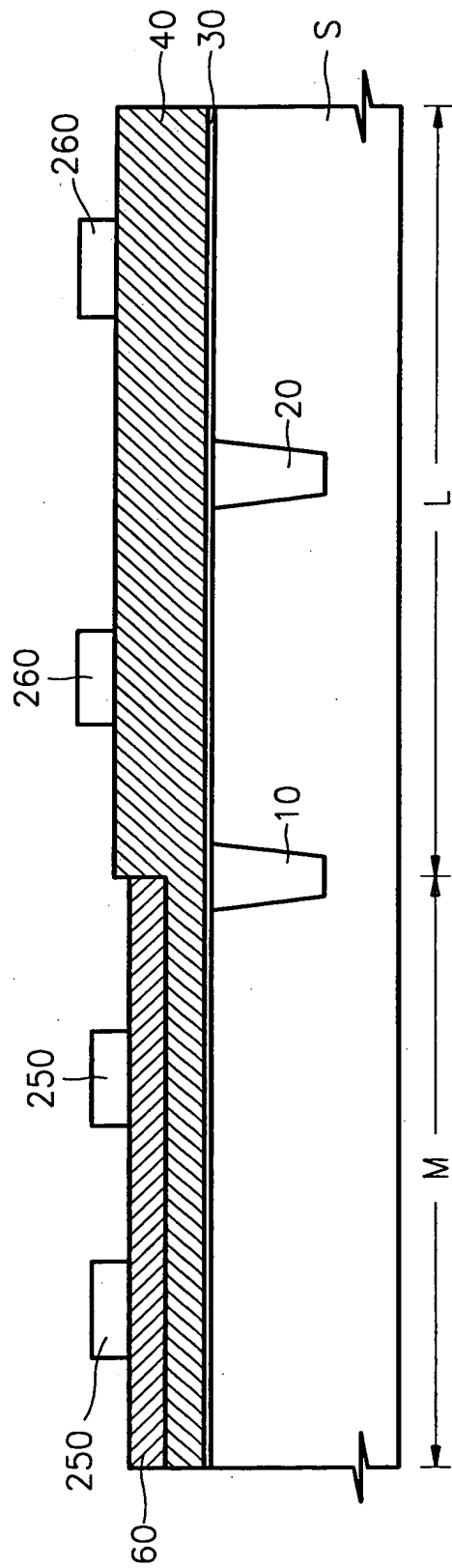
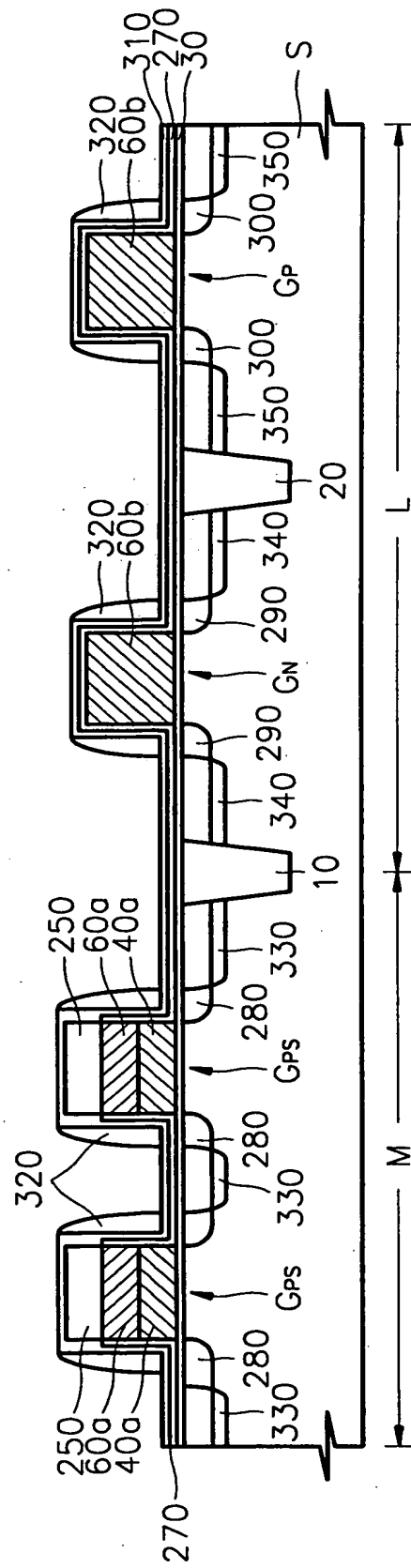


FIG. 2B



This cross-sectional view shows a semiconductor device with a central channel region 300. The device features a series of gate regions 320, 340, and 360, which are separated by spacers 350 and 370. The gate regions 320 and 340 are connected to a common gate electrode 330. The gate regions 360 are connected to a common gate electrode 330. The device is formed on a substrate 310, which is covered by a passivation layer 300. The device is labeled with various dimensions and parameters, including L, M, and S.

Fig. 6 shows a cross-sectional view of a multi-layered substrate assembly. The assembly includes several layers and components, with labels indicating specific parts and dimensions. Key features include:

- Layers and Components:** 270, 360, 370, 250, 60c, 40c, 320, 280, 330, 280, GPs, 330, 280, 330, 280, 340, 290, GN, 290, 340, 20, 350, 300, GP, 300, 350, 380, 310, 320, 60b, 380, and S.
- Dimensions:** M (width), L (length), and 10 (thickness).

